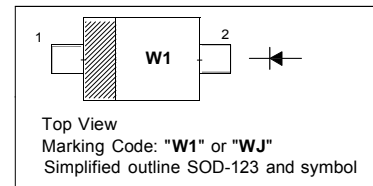


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1 2	A
		at $t = 1\text{ s}$ at $t = 1\text{ }\mu\text{s}$	
Power Dissipation	P_{tot}	400	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	312	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	1	V
Reverse Breakdown Voltage at $I_R = 5\text{ }\mu\text{A}$ at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$ $V_{(BR)R}$	75 100	- -	V V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	I_R	- - -	25 5 50	nA μA μA
Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	4	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}$, $I_{rr} = 3\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}	-	50	ns